





N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

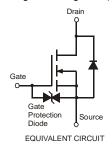
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- ESD Protected Up To 2kV
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability

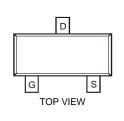
Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.008 grams (approximate)









Maximum Ratings @ $T_A = 25$ °C unless otherwise specified

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±20	V
Drain Current (Note 1)	Continuous Pulsed (Note 3)	I _D	300 800	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_d	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +150	°C

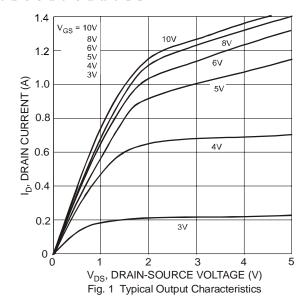
Electrical Characteristics @T_A = 25°C unless otherwise specified

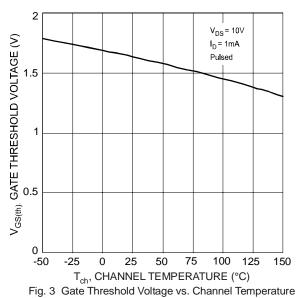
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)	•	-	•			•
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μА	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)	•		•			
Gate Threshold Voltage	V _{GS(th)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$
Static Drain-Source On-Resistance	В		_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Dialii-Source Off-Resistance	R _{DS} (ON)		_	3.0	5.2	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	_	50	pF	V 05V V 0V
Output Capacitance	C _{oss}	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	_	5.0	pF	11 = 1.0IVII IZ

Note:

- 1. Device mounted on FR-4 PCB.
- 2. No purposefully added lead.
- Pulse width ≤10µS, Duty Cycle ≤1%.
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 5. Short duration pulse test used to minimize self-heating effect.







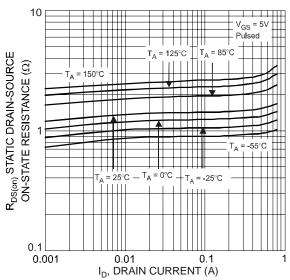
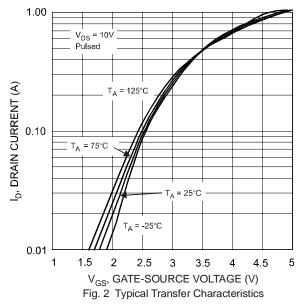


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



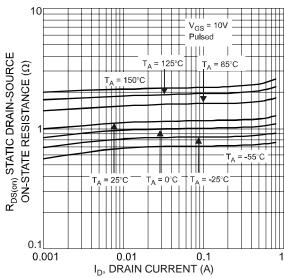


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

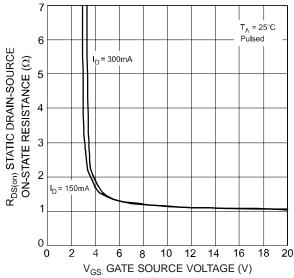
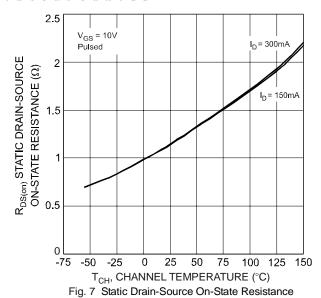
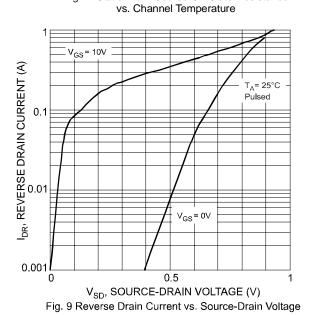
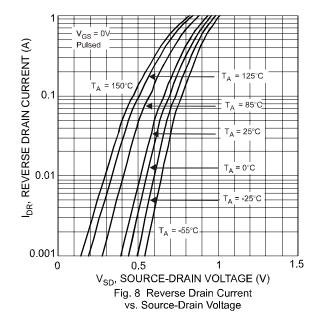


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage









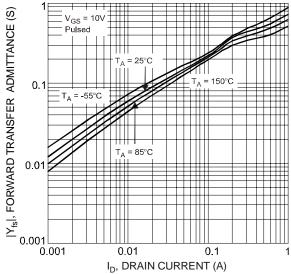


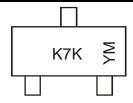
Fig.10 Forward Transfer Admittance vs. Drain Current

Ordering Information (Note 6)

ſ	Part Number	Case	Packaging
	2N7002K-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



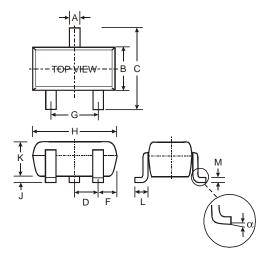
K7K = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	\	٧	Х		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

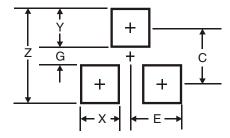


Package Outline Dimensions



SOT-23				
Dim	Min	Max		
Α	0.37	0.51		
В	1.20	1.40		
С	2.30	2.50		
D	0.89	1.03		
F	0.45	0.60		
G	1.78	2.05		
Н	2.80	3.00		
J	0.013	0.10		
K	0.903	1.10		
L	L 0.45 0.6			
M	0.085	0.180		
α	0°	8°		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
X	0.9
Y	1.4
С	2.0
E	0.9

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